

## **NPN BUX98**

# **HIGH VOLTAGE FAST SWITCHING**

The BUX98 is silicon multiepitaxial NPN transistor in Jedec TO-3.

They are intended and industrial applications from single and three-phase mains operation. Compliance to RoHS.

#### **ABSOLUTE MAXIMUM RATINGS**

Symbol	Ratings		Value	Unit
V <sub>CEO</sub>	Collector-Emitter Voltage	$I_B = 0$	400	V
V <sub>CBO</sub>	Collector-Base Voltage	$V_{BE} = 0$	850	V
$V_{EBO}$	Emitter-Base Voltage	$I_C = 0$	7	
Ic	Collector Current		30	Α
I <sub>CM</sub>	Collector Peak Current	$t_p = <5ms$	60	Α
I <sub>CP</sub>	Collector Peak Current non Rep.	$t_p = <20 \mu s$	80	А
I <sub>B</sub>	Base Current		8	Α
I <sub>BM</sub>	Base Peak Current	$t_p = <5ms$	30	А
P <sub>t</sub>	Total Power Dissipation	$@ T_C = 25^\circ$	250	Watts
TJ	Junction Temperature		200	°C
T <sub>Stg</sub>	Storage Temperature		-65 to +200	°C

#### THERMAL CHARACTERISTICS

Symbol	Ratings	Value	Unit
R <sub>thJC</sub>	Thermal Resistance, Junction to Case	0.7	°C/W



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# **ELECTRICAL CHARACTERISTICS**

TC=25°C unless otherwise noted

Symbol	Ratings	Test Condition(s)	Min	Тур	Max	Unit
V <sub>CEO(SUS)</sub>	Collector-Emitter Sustaining Voltage (*)	I <sub>C</sub> =100 mA	700	1	-	V
		$V_{CE} = V_{CES}$ , $R_{BE} = 10\Omega$	-	-	1	
I <sub>CER</sub>	Collector Cutoff Current	$V_{CE} = V_{CES}$ , $R_{BE} = 10\Omega$ $T_{CASE} = 125^{\circ}C$	-	-	8	mA
I <sub>CEO</sub>	Collector Cutoff Current	$V_{CE} = V_{CEO}$ , $I_B = 0A$	-	1	2	mA
		$V_{CE} = V_{CES}$ , $V_{BE} = 0$	-	ı	1	
I <sub>CES</sub>	Collector Cutoff Current	$V_{CE} = V_{CES}$ , $V_{BE} = 0$ $T_{CASE} = 125$ °C	-	-	6	mA
I <sub>EBO</sub>	Emitter Cutoff Current	$V_{EB} = 5.0 \text{ V}, I_{C} = 0$	-	-	2	mΑ
	Collector-Emitter saturation	$I_{C} = 12 \text{ A}$ , $I_{B} = 3 \text{ A}$	-	-	1.5	
V <sub>CE(SAT)</sub>	Voltage (*)	$I_{C} = 16 \text{ A}$ , $I_{B} = 5 \text{ A}$	-	-	2	V
, ,		$I_{C} = 20 \text{ A}$ , $I_{B} = 8 \text{ A}$	-	-	3	
V	Base-Emitter saturation Voltage	$I_{C} = 12 \text{ A}$ , $I_{B} = 3 \text{ A}$	-	-	1.6	
V <sub>BE(SAT)</sub>	(*)	$I_{C} = 20 \text{ A}$ , $I_{B} = 8 \text{ A}$	-	-	2	
t <sub>on</sub>	Turn-on time	RESISTIVE LOAD	-	0.5	1	
t <sub>s</sub>	Storage time	$I_{C}=8 \text{ A}, I_{B}=1 \text{ A}$ $V_{CC}=150 \text{ V}$	-	1.5	3	μs
t <sub>f</sub>	File time	$I_{C}=12 \text{ A}$ , $V_{CC}=250 \text{ V}$ $I_{B1}=-I_{B2}=3 \text{ A}$	-	0.2	0.8	

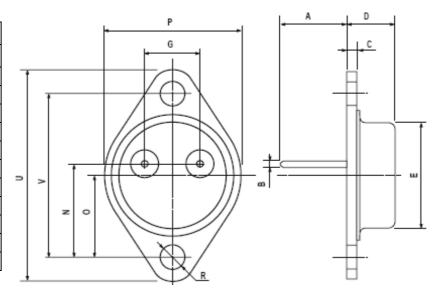
<sup>(\*)</sup> Pulse Duration = 300  $\mu$ s, Duty Cycle  $\leq$  1.5%



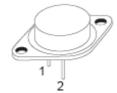
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### **MECHANICAL DATA CASE TO-3**

DIMENSIONS (mm)			
	min	max	
A	11	13.10	
В	0.97	1.15	
С	1.5	1.65	
D	8.32	8.92	
F	19	20	
G	10.70	11.1	
N	16.50	17.20	
Р	25	26	
R	4	4.09	
U	38.50	39.30	
V	30	30.30	



Pin 1 :	Base
Pin 2 :	Emitter
Case:	Collector



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